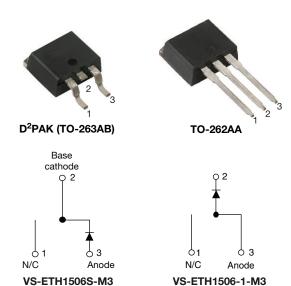


VS-ETH1506SHM3, VS-ETH1506-1HM3

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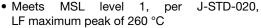
Hyperfast Rectifier, 15 A FRED Pt®



PRIMARY CHARACTERISTICS						
I _{F(AV)}	15 A					
V_{R}	600 V					
V _F at I _F	1.25 V					
t _{rr} (typ.)	21 ns					
T _J max.	175 °C					
Package	D ² PAK (TO-263AB), TO-262AA					
Circuit configuration	Single					

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- AEC-Q101 qualified, meets JESD 201 class 1A whisker test



 Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

AUTOMOTIVE GRADE Available







DESCRIPTION / APPLICATIONS

Hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC Boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS					
Repetitive peak reverse voltage	V _{RRM}		600	V					
Average rectified forward current	I _{F(AV)}	T _C = 139 °C	15	۸					
Non-repetitive peak surge current	I _{FSM}	T _C = 25 °C	160	A					
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C					

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-	V		
Famous de la contraction de la	V _F	I _F = 15A	-	1.8	2.45	V		
Forward voltage		I _F = 15 A, T _J = 150 °C	-	1.25	1.6			
Reverse leakage current	I_	$V_R = V_R$ rated	-	0.01	15			
Reverse leakage current I _R		$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	20	200	μΑ		
Junction capacitance	C _T	$V_{R} = 600 \text{ V}$	-	12	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nΗ		

VS-ETH1506SHM3, VS-ETH1506-1HM3

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
		I _F = 1.0 A, dI _F /dt =	$100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$	-	21	26		
Reverse recovery time	+	$I_F = 1.5 A, dI_F/dt =$	100 A/ μ s, V _R = 30 V	-	25	36	ne	
Heverse recovery time	t _{rr}	T _J = 25 °C		-	29	-	ns -	
		T _J = 125 °C	$I_F = 15 A$ $dI_F/dt = 200 A/\mu s$	-	65	-		
Peak recovery current	1	T _J = 25 °C		-	3.9	-	A	
reak recovery current	I _{RRM}	T _J = 125 °C	$V_{\rm R} = 390 \text{ V}$	-	7.0	-		
Doverse receivery charge	0	T _J = 25 °C	v _R = 390 v	-	60	-	nC	
Reverse recovery charge	Q_{rr}	T _J = 125 °C		-	240	-	110	
Reverse recovery time	t _{rr}		I _F = 15 A	-	42	-	ns	
Peak recovery current	I _{RRM}	T _J = 125 °C	$dI_F/dt = 800 A/\mu s$	-	21	-	Α	
Reverse recovery charge	Q _{rr}		V _R = 390 V	-	480	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C			
Thermal resistance, junction to case	R _{thJC}		-	1.3	1.51	°C/W			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	70				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-				
Maight			-	2.0	-	g			
Weight			-	0.07	-	OZ.			
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)			
Mayling daying		Case style D ² PAK (TO-263AB)	ETH1506SH			•			
Marking device		Case style TO-262AA		ETH15	506-1H				

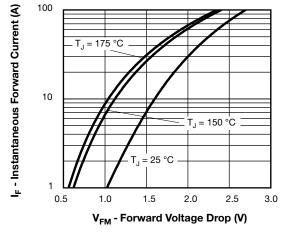


Fig. 1 - Typical Forward Voltage Drop Characteristics

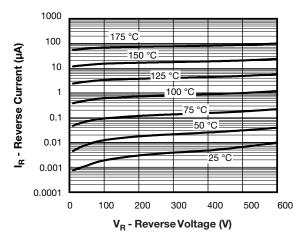


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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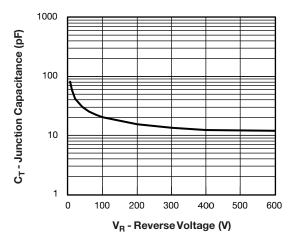


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

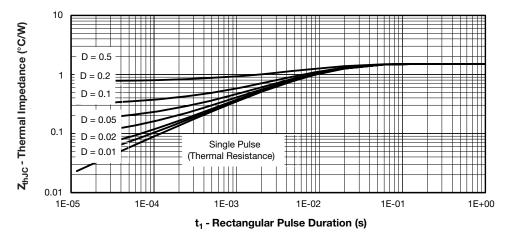


Fig. 4 - Max. Thermal Impedance Z_{thJC} Characteristics

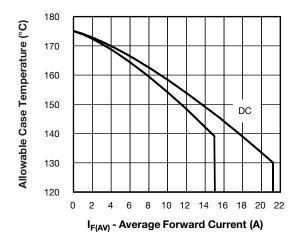


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

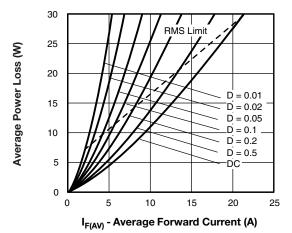


Fig. 6 - Forward Power Loss Characteristics

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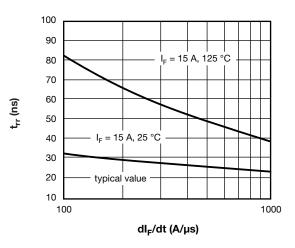


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

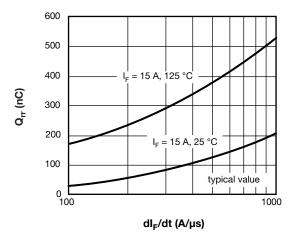


Fig. 8 - Typical Stored Charge vs. dl_F/dt

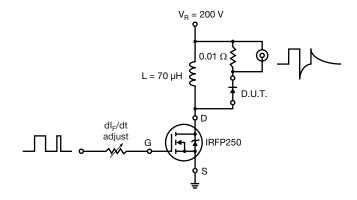
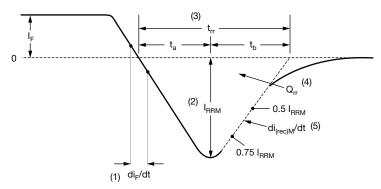


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_{r}$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

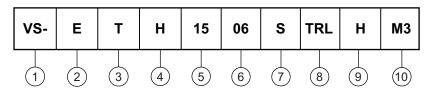
Fig. 10 - Reverse Recovery Waveform and Definitions

VS-ETH1506SHM3, VS-ETH1506-1HM3

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

Circuit configuration
E = single diode

3 - T = TO-220

4 - H = Hyperfast recovery time

5 - Current code (15 = 15 A)

6 - Voltage code (06 = 600 V)

7 - • S = D²PAK

- • -1 = TO-262

8 - • None = tube

TRL = tape and reel (left oriented, for D²PAK package)

- • TRR = tape and reel (right oriented, for D²PAK package)

9 - H = AEC-Q101 qualified

10 - Environmental digit:

M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION					
VS-ETH1506SHM3	50	Antistatic plastic tube					
VS-ETH1506-1HM3	50	Antistatic plastic tube					
VS-ETH1506STRRHM3	800	13" diameter reel					
VS-ETH1506STRLHM3	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS						
Dimensions	D ² PAK (TO-263AB)	www.vishay.com/doc?95046				
Differsions	TO-262AA	www.vishay.com/doc?95419				
Dort marking information	D ² PAK (TO-263AB)	www.vishay.com/doc?95444				
Part marking information	TO-262AA	www.vishay.com/doc?95443				
Packaging information	D ² PAK (TO-263AB)	www.vishay.com/doc?95032				



Vishay Semiconductors

D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		HES NOTES		SYMBOL	MILLIMETERS		MILLIMETERS INCHES		HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	NOIES	STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3	
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3	
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3	
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC		
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625		
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110		
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3	
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070		
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC		
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208		

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB

Vishay Semiconductors

TO-262

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	METERS	INC	INCHES		
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	2.03	3.02	0.080	0.119		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	
D1	6.86	8.00	0.270	0.315	3	
E	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54 BSC		0.100	BSC		
L	13.46	14.10	0.530	0.555		
L1	-	1.65	-	0.065	3	
L2	3.36	3.71	0.132	0.146		

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- 5) Controlling dimension: inches
- (6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum), D1 (minimum) and L2 where dimensions derived the actual package outline

Revision: 11-Jul-2019 1 Document Number: 95419



Legal Disclaimer Notice

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